

# Silicon Variable Capacitance Diode

- For FM radio tuner with extended frequency band 77MHz to 108MHz
- Designed for application requiring back-to-back diode configuration for optimum signal distortion and detuning
- High tuning ratio at low supply voltage (car radio)
- Monolitic chip (common cathode) for perfect dual diode tracking
- Good C- V linearity
- High figure of merit
- Pb-free (RoHS compliant) package



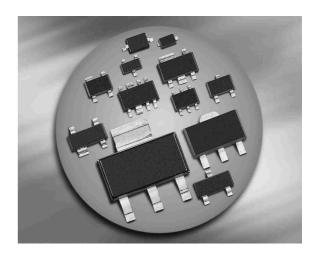
## BB844



Туре	Package	Configuration	L <sub>S</sub> (nH)	Marking
BB844	SOT23	common cathode	1.8	SNs

## **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V <sub>R</sub>	18	V	
Peak reverse voltage	V <sub>RM</sub>	20		
Forward current	I <sub>F</sub>	50	mA	
Operating temperature range		-55 150	°C	
Storage temperature	T <sub>stq</sub>	-55 150		





Parameter	Symbol	Values			Unit
		min.	typ.	max.	]
DC Characteristics					
Reverse current	I <sub>R</sub>				nA
<i>V</i> <sub>R</sub> = 16 V		-	-	20	
V <sub>R</sub> = 16 V, <i>T</i> <sub>A</sub> = 85 °C		-	-	200	
AC Characteristics					
Diode capacitance	CT				pF
V <sub>R</sub> = 2 V, <i>f</i> = 1 MHz		42.5	43.75	45	
V <sub>R</sub> = 4 V, <i>f</i> = 1 MHz		25	27	29	
<i>V</i> <sub>R</sub> = 8 V, <i>f</i> = 1 MHz		10	11.5	13	
Capacitance ratio	C <sub>T2</sub> /C <sub>T8</sub>	3.2	3.8	-	
V <sub>R</sub> = 2 V, V <sub>R</sub> = 8 V, <i>f</i> = 1 MHz					
Capacitance matching <sup>1)</sup>	∆C <sub>T</sub> /C <sub>T</sub>	-	-	1.5	%
$V_{\rm R}$ = 2V to 8V , $f$ = 1 MHz					
Series resistance	r <sub>S</sub>	-	0.28	-	Ω
V <sub>R</sub> = 2 V, <i>f</i> = 100 MHz					

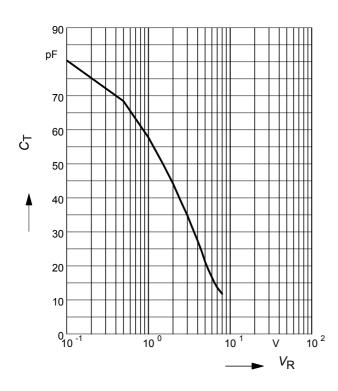
# **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

<sup>1</sup>For details please refer to Application Note 047.

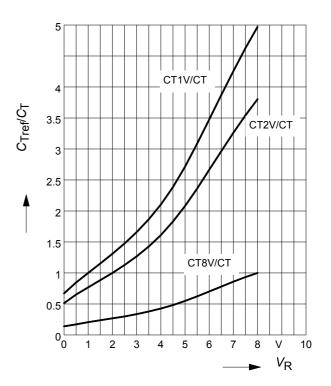


**Diode capacitance**  $C_{T} = f(V_{R})$ 

f = 1 MHz



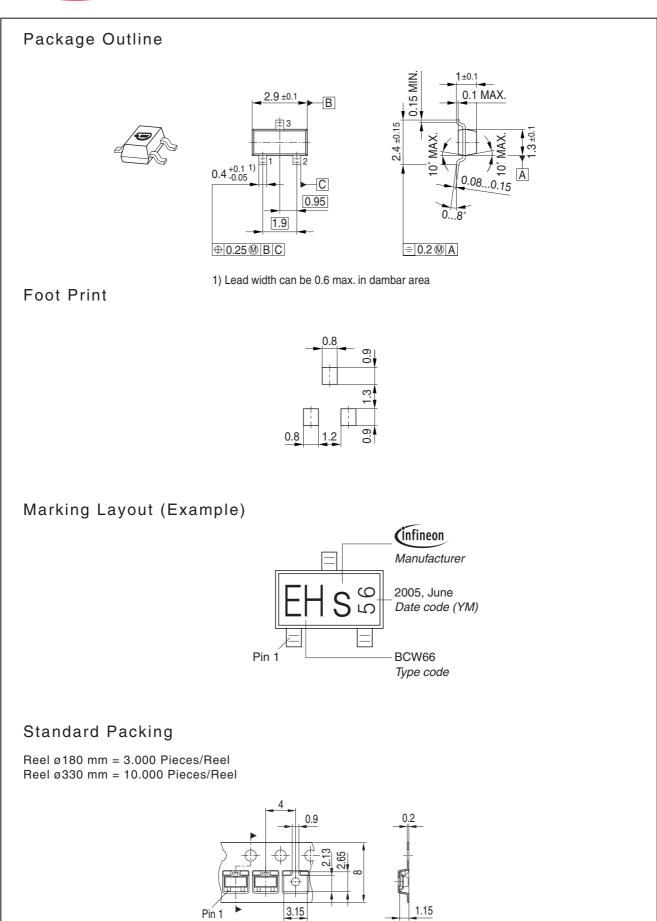
**Capacitance ratio**  $C_{\text{Tref}}/C_{\text{T}} = f(V_{\text{R}})$ f = 1MHz



# Temperature coefficient of the diode capacitance $T_{CC} = f(V_R)$









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